SG2M023120LJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

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TO-247-4L

Benefits

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-
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Applications

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-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on),\ typ}$	$T_{J,max}$	Marking	Package

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1 Maximum ratings

Table 2 Maximum rating

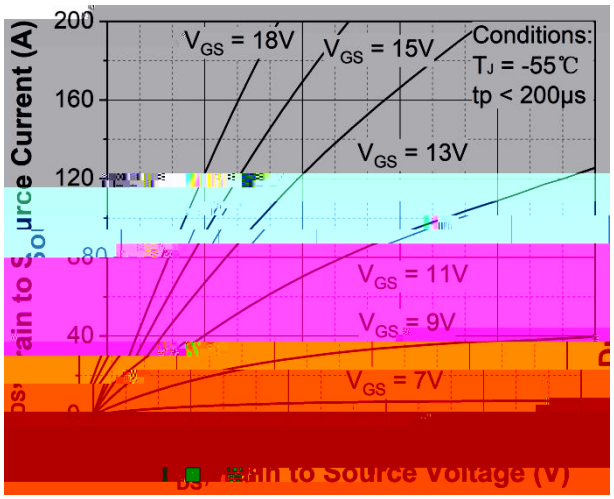
Symbol	Parameter	Value	Unit

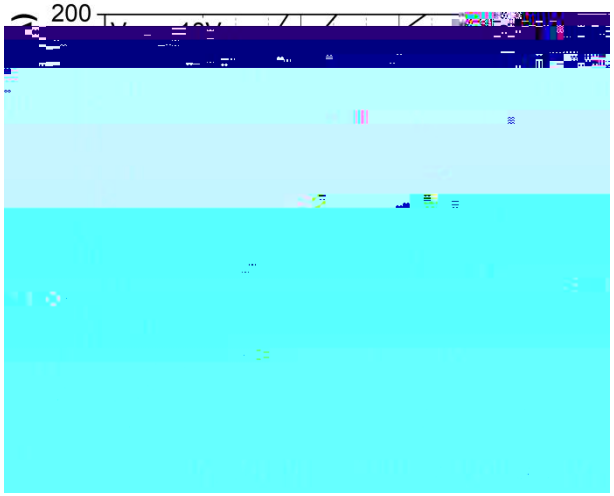
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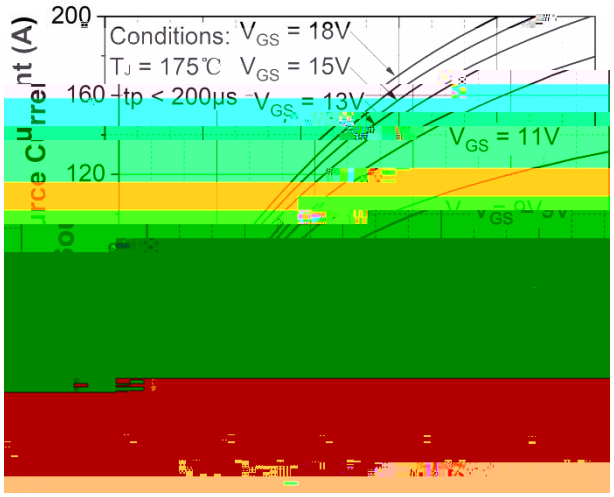
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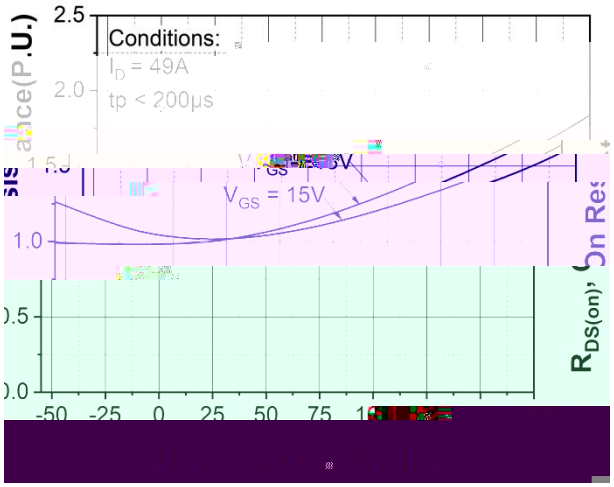
1200V SiC Power MOSFE

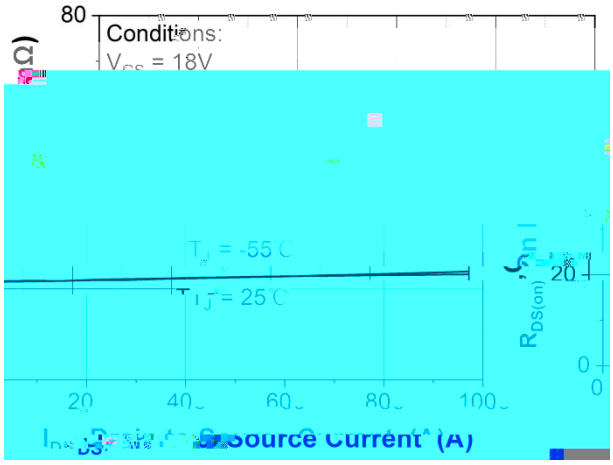
4 Electrical characteristic diagrams

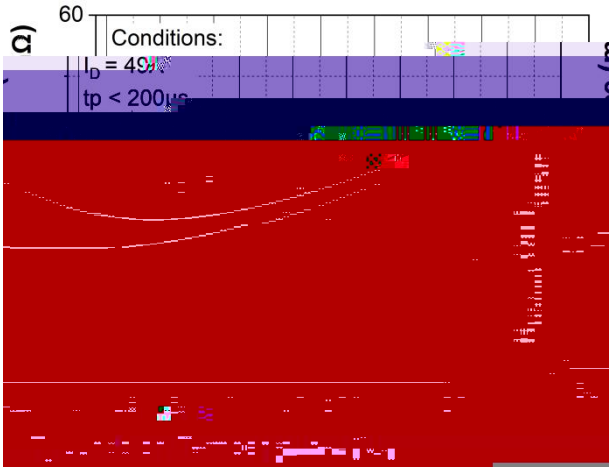




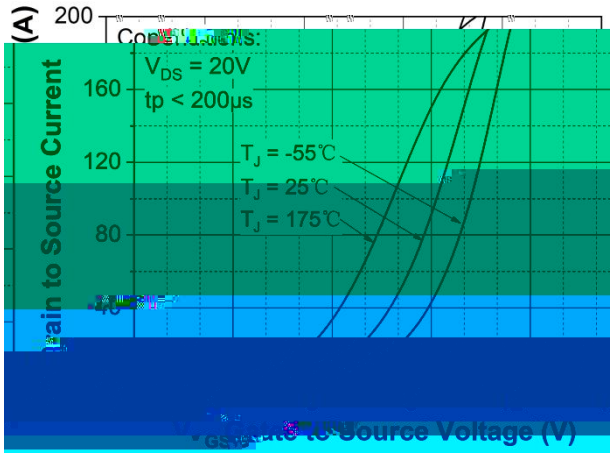


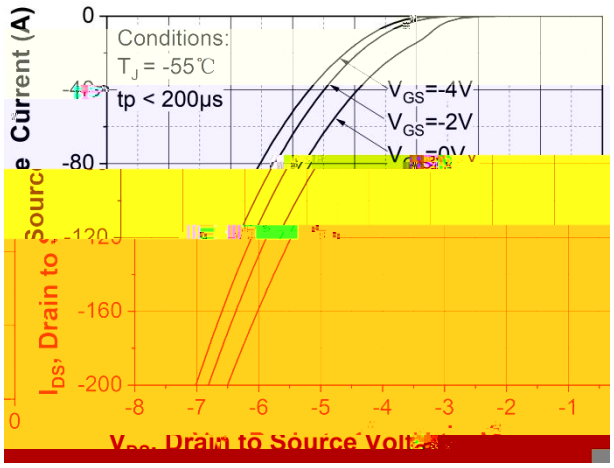


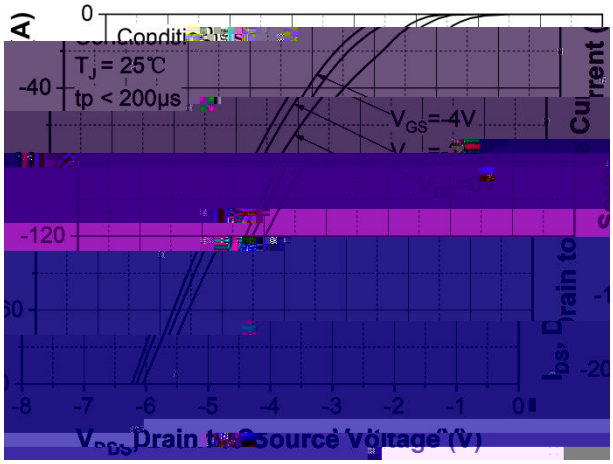


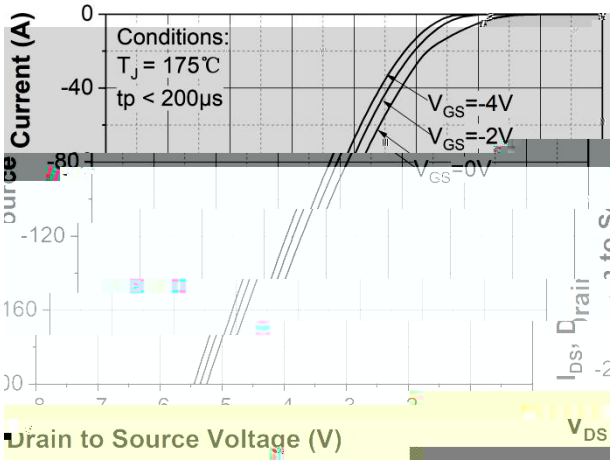


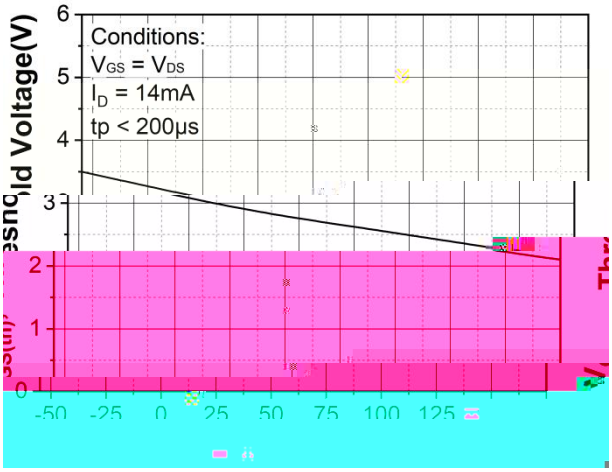
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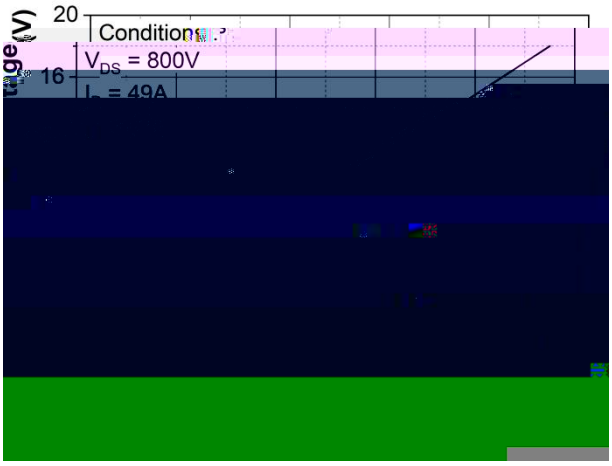




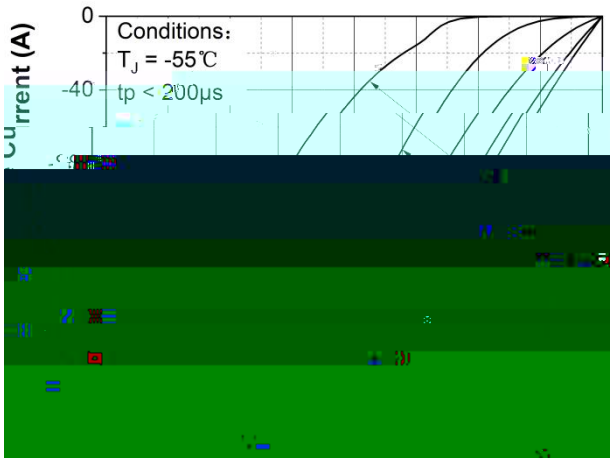


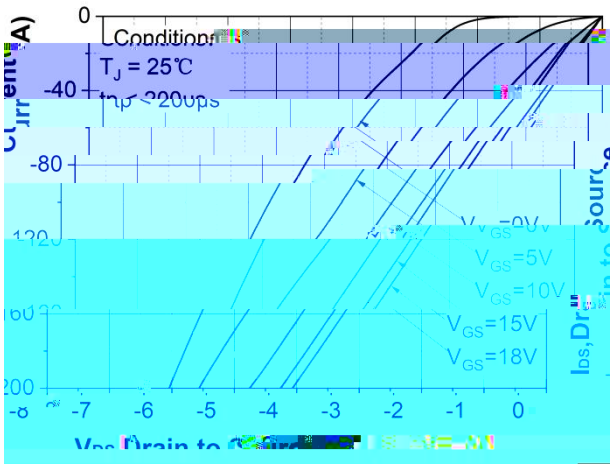


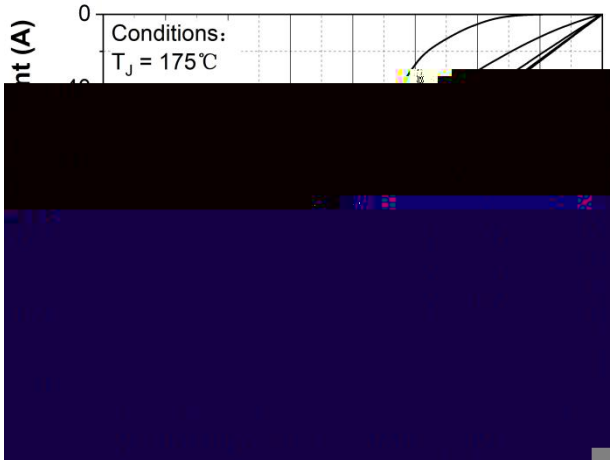


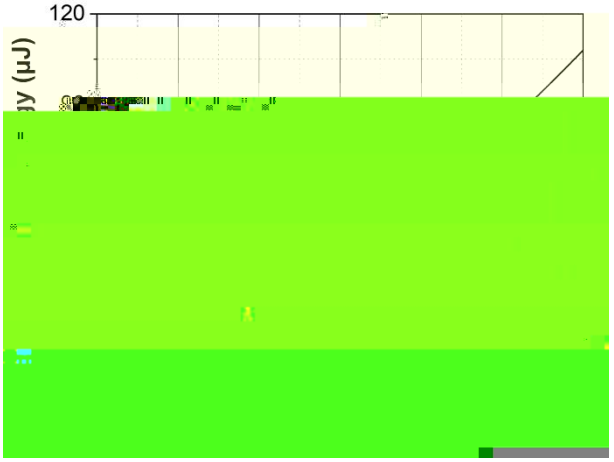


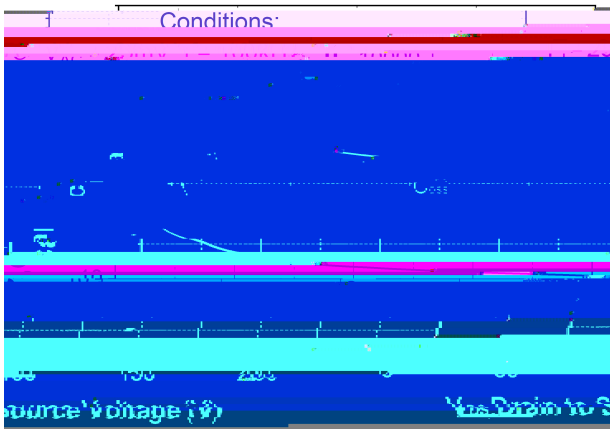
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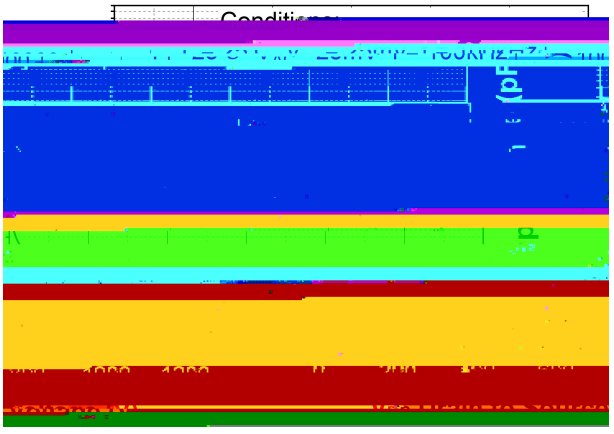




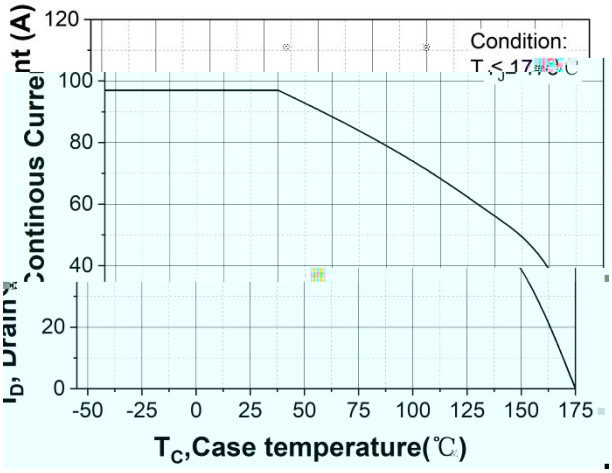


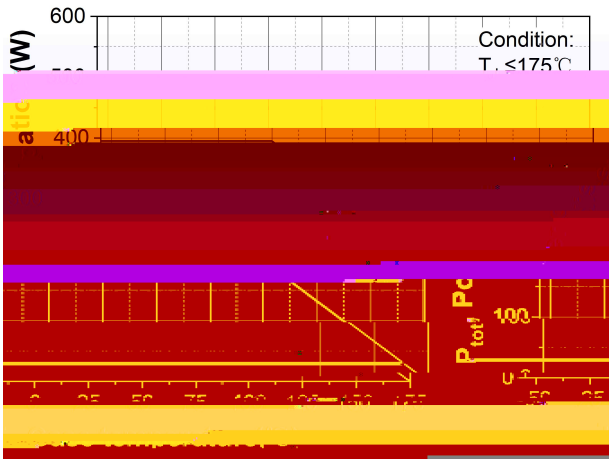


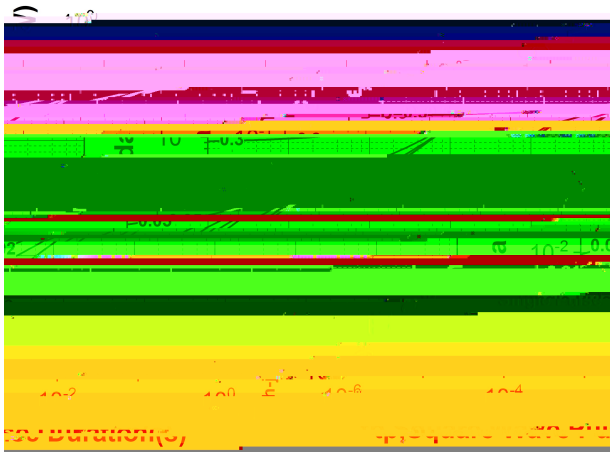


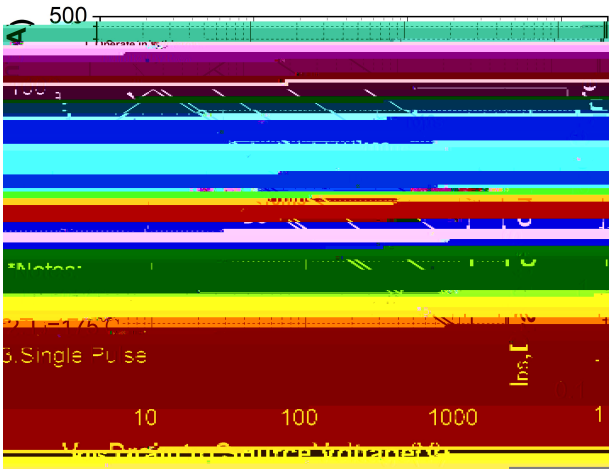


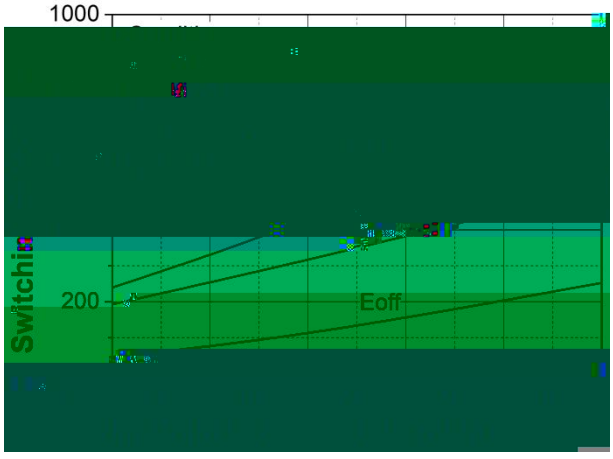
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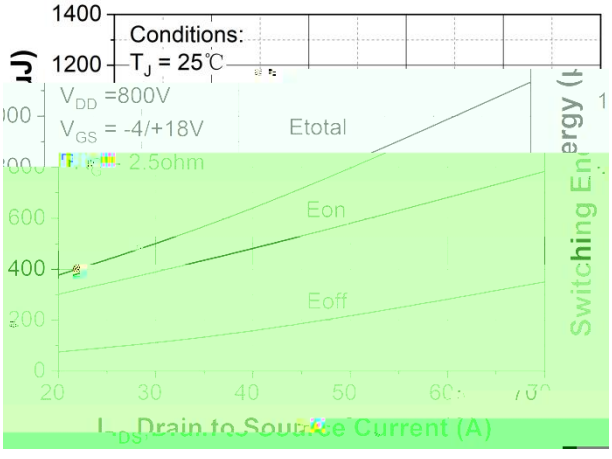




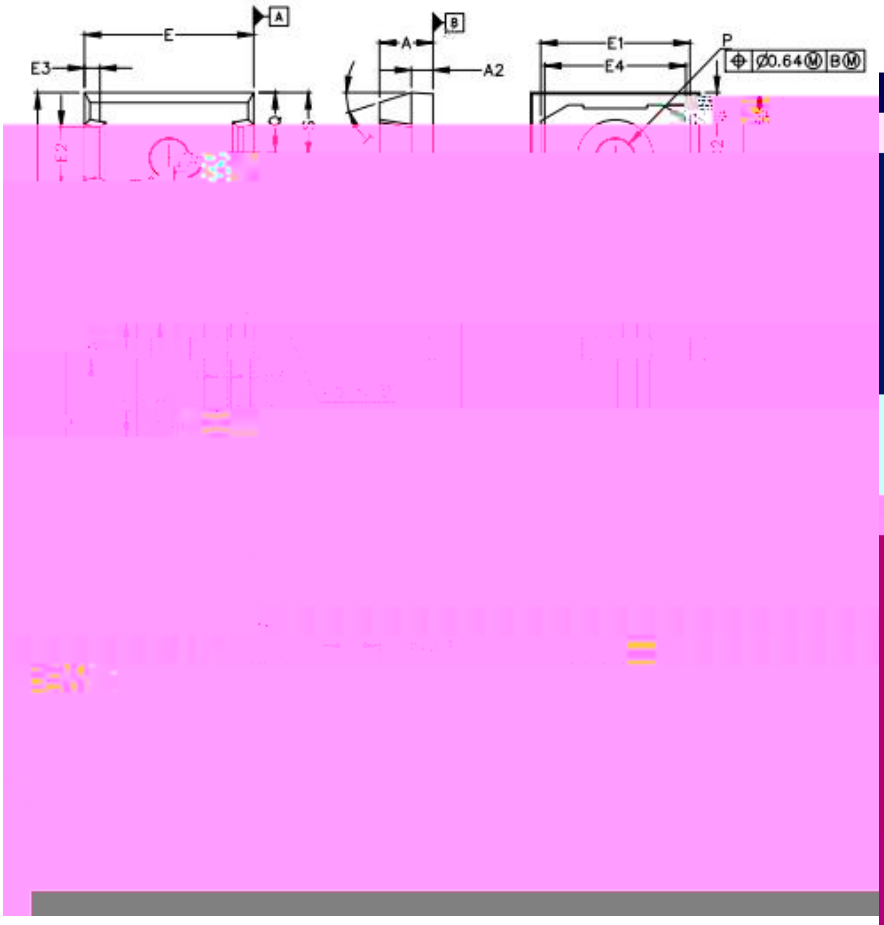






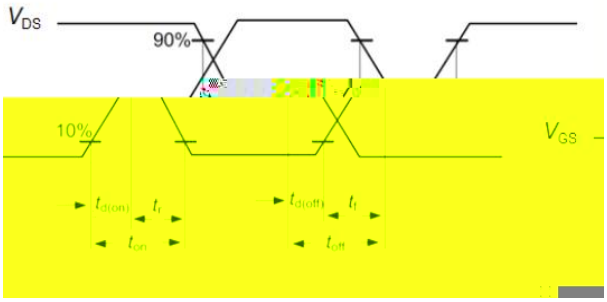


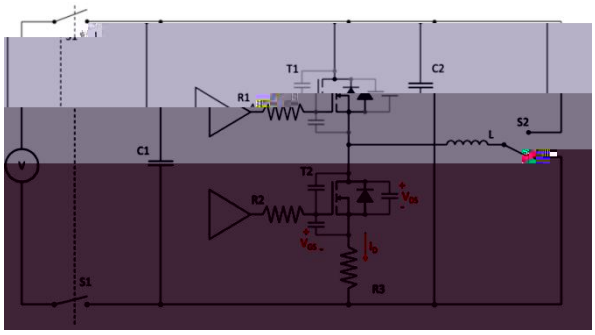
5 Package drawing



NOTE ;
1. ALL METAL SURFACES: TIN PLATED,EXCEPT AREA OF CUT
2. DIMENSIONING & TOLERANCEING CONFIRM TO
ASME

6 Test conditions





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1200[illegible]C Power MOS[illegible]T

Re[illegible]ion history

Document version	Date of release	Document stage	Description of changes
V01_00	2024-11-20	——	——
V01_01	2025-08-28	——	——
V01_02	2025-11-12	——	——
V01_03	2025-12-22	Final	——

Attention

RoHS compliance

SG2M023120LJ